

## Silicon PNP Power Transistors

2SA837

## DESCRIPTION

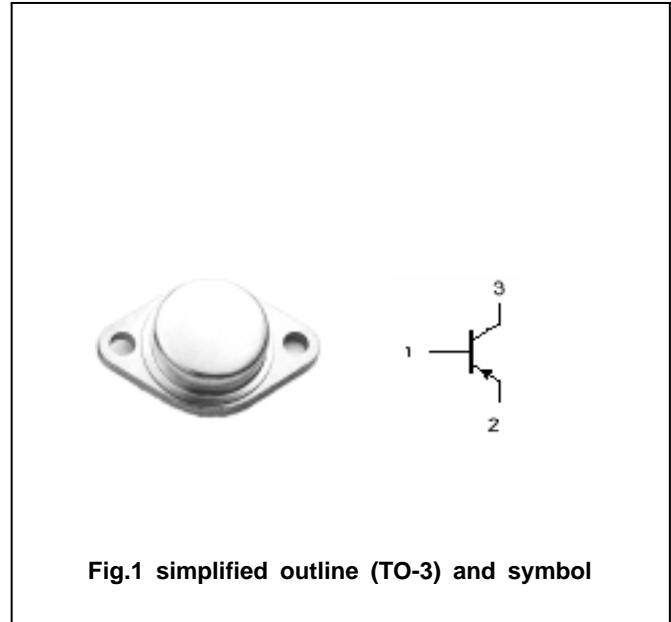
- With TO-3 package
- Wide area of safe operation
- Complement to type 2SC1667

## APPLICATIONS

- For radio frequency and power amplifier applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a =$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-90	V
$V_{CEO}$	Collector-emitter voltage	Open base	-90	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-4	A
$P_C$	Collector power dissipation	$T_C=75$	50	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA; I <sub>B</sub> =0	-90			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> =0	-90			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-90V; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-4V	40		200	
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz		200		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A; V <sub>CE</sub> =-10V		10		MHz

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PACKAGE OUTLINE

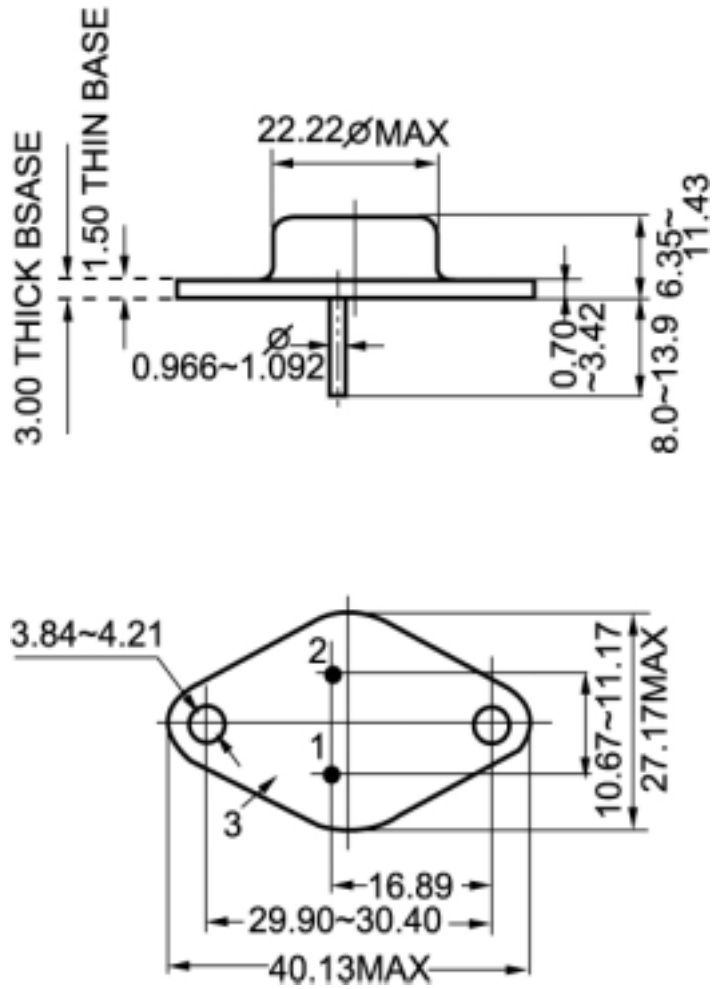


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.1\text{mm}$ )